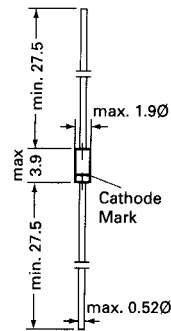


# ST 60 P

## SILICON SCHOTTKY BARRIER DIODE

**Silicon Schottky Barrier Diode**  
Characteristics equivalent to or better than 1N60P  
ideal for used in detection or for switching on the  
radio, TV, etc..



Glass case JEDEC DO-35

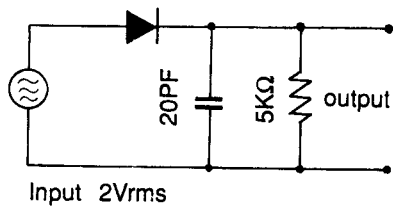
Dimensions in mm

**Absolute Maximum Ratings** ( $T_a = 25\text{ }^{\circ}\text{C}$ )

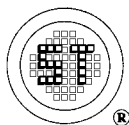
|                                  | Symbol      | Value        | Unit               |
|----------------------------------|-------------|--------------|--------------------|
| Peak Reverse Voltage             | $V_{RM}$    | 45           | V                  |
| Reverse Voltage dc               | $V_R$       | 20           | V                  |
| Peak Forward Current             | $I_{FM}$    | 150          | mA                 |
| Average Rectified Output Current | $I_O$       | 50           | mA                 |
| Surge Forward Current            | $I_{surge}$ | 500          | mA                 |
| Junction Temperature             | $T_J$       | 75           | $^{\circ}\text{C}$ |
| Storage Temperature Range        | $T_S$       | -55 to + 175 | $^{\circ}\text{C}$ |

**Characteristics**

|                          | Symbol | Test condition ( $T_a\ 25 \pm 2\text{ }^{\circ}\text{C}$ )                      | Min. | Typ. | Max. | Units         |
|--------------------------|--------|---|------|------|------|---------------|
| Forward Current          | $I_F$  | $V_F = 1\text{V}$   | 4    | -    | -    | mA            |
| Reverse Currents         | $I_R$  | $V_R = 10\text{V}$  | -    | -    | 50   | $\mu\text{A}$ |
| Junction Capacitance C.  | -      | $f = 1\text{MHz}, V = 1\text{V}$  | -    | -    | 1    | PF            |
| Rectification efficiency | $\eta$ | $V_i = 2\text{Vrms}, = 5\text{K}\Omega$<br>$C = 20\text{PF}, f = 40\text{ MHz}$ | 55   | -    | -    | %             |



**Rectification Efficiency Measurement Circuit**



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